35th RD50 Workshop (CERN)

Wednesday, 20 November 2019

Sensor Characterization Techniques (TCT, CV); Extreme Fluences: Sensor Characterization Techniques (TCT, CV); Extreme Fluences - 30/7-018 - Kjell Johnsen Auditorium (09:00 - 14:00)

-Conveners: Marcos Fernandez Garcia; Gregor Kramberger

time	[id] title	presenter
09:00	[14] Effective trapping probability of electrons in neutron irradiated Si detectors using Transient Current Technique simulations	Mr JAIN, Chakresh
09:20	[34] TPA-TCT -- Two Photon Absorption - Transient Current Technique	WIEHE, Moritz Oliver
09:40	[22] Plasma Effects in TCT-TPA	PALOMO PINTO, Francisco Rogelio
10:00	[1] Measurements with Si detectors irradiated to extreme fluences	MANDIC, Igor
10:20	[17] Effects of trapping on the collected signals from subsequent laser pulses in irradiated silicon sensors	DIEHL, Leena
10:40	Coffee Break	
11:10	[4] Determination of the electric field in highly-irradiated silicon sensors using edge-TCT measurements	KRAMBERGER, Gregor
11:30	[25] Characterisation of 3D pixel sensors irradiated at extreme fluences	MANNA, Maria
11:50	[37] Discussion Session: TCT, Extreme Fluences and Modelling	KRAMBERGER, Gregor